

# The RF Line NPN Silicon High-Frequency Transistor

**MRF9331LT1**

Designed primarily for use in low power amplifiers to 1.0 GHz. Ideal for pagers and other battery operated systems where low power consumption is critical.

- Low Power Consumption Characterized for  $I_E = 0.1$  to 1.0 mA
- High Current-Gain — Bandwidth Product —  
 $f_T = 5.0$  GHz (Typ) @  $I_C = 1.0$  mAdc
- Low Noise Figure and High Power Gain @  $f = 1.0$  GHz —  
NF(matched) = 2.5 dB (Typ)  
GNF(matched) = 12.5 dB (Typ)
- Guaranteed RF Parameters
- Surface Mounted SOT-143 Offers Improved RF Performance  
Lower Package Parasitics  
High Gain
- Available in tape and reel packaging:  
T1 suffix = 3,000 units per reel

$I_C = 1.0$  mA  
SURFACE MOUNTED  
HIGH-FREQUENCY  
TRANSISTOR  
NPN SILICON



CASE 318A-05, STYLE 1  
SOT-143  
LOW PROFILE

## MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	8.0	Vdc
Collector-Base Voltage	$V_{CBO}$	15	Vdc
Emitter-Base Voltage	$V_{EBO}$	2.0	Vdc
Collector Current — Continuous	$I_C$	2.0	mAdc
Total Device Dissipation @ $T_C = 100^\circ\text{C}$ (1) Derate above $100^\circ\text{C}$	$P_D$	50 1.0	mW mW/ $^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to +150	$^\circ\text{C}$

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1000	$^\circ\text{C}/\text{W}$

## DEVICE MARKING

MRF9331LT1 = 05

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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## OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ( $I_C = 1.0$ mAdc, $I_B = 0$ )	$V_{(BR)CEO}$	8.0	—	—	Vdc
Collector-Base Breakdown Voltage ( $I_C = 0.01$ mAdc, $I_E = 0$ )	$V_{(BR)CBO}$	15	—	—	Vdc
Emitter-Base Leakage Current ( $V_{EB} = 2.0$ Vdc, $I_C = 0$ )	$I_{EBO}$	—	—	0.1	mAdc
Collector Cutoff Current ( $V_{CB} = 5.0$ Vdc, $I_E = 0$ )	$I_{CBO}$	—	—	50	nAdc

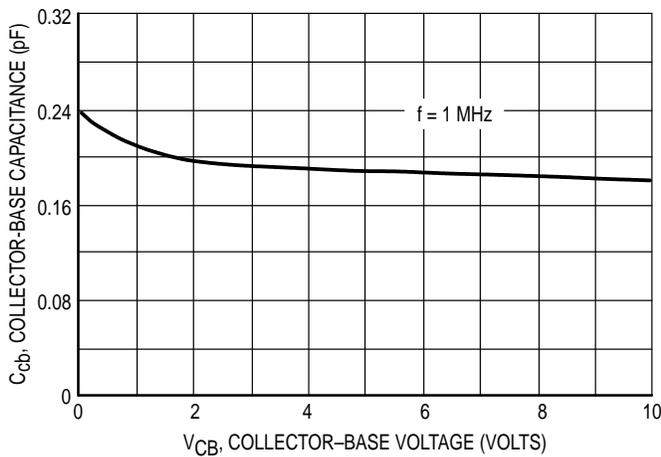
NOTE:

1. Case temperature measured on collector lead immediately adjacent to body of package.

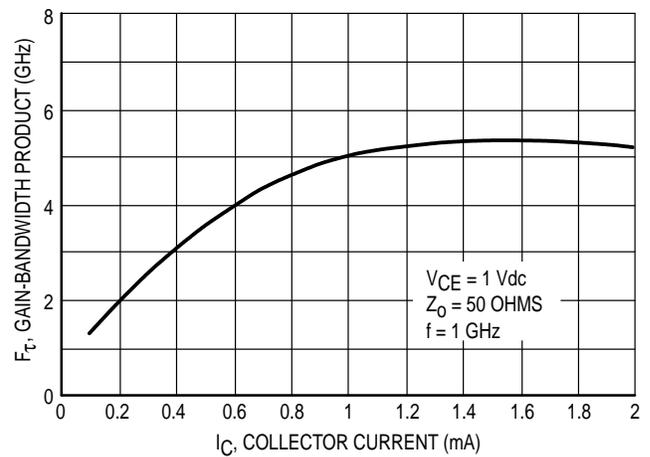
(continued)

**ELECTRICAL CHARACTERISTICS — continued** ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

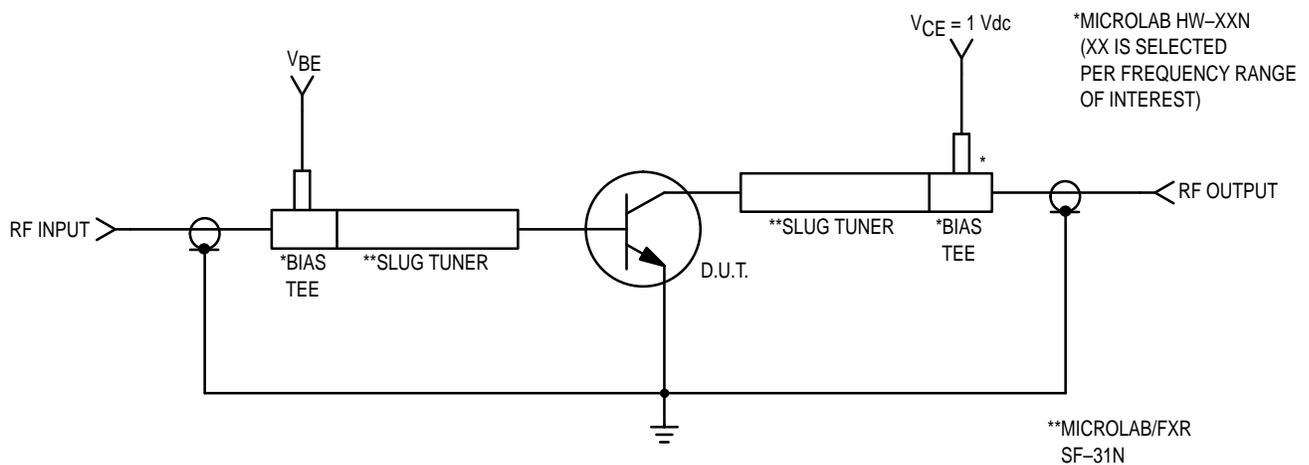
Characteristic	Symbol	Min	Typ	Max	Unit
<b>ON CHARACTERISTICS</b>					
DC Current Gain ( $I_C = 0.5\text{ mA}$ , $V_{CE} = 1.0\text{ Vdc}$ )	$h_{FE}$	30	80	200	—
<b>DYNAMIC CHARACTERISTICS</b>					
Current-Gain — Bandwidth Product ( $I_C = 1.0\text{ mA}$ , $V_{CE} = 1.0\text{ Vdc}$ , $f = 1.0\text{ GHz}$ )	Figure 2 $f_T$	3.5	5.0	—	GHz
Collector-Base Capacitance ( $V_{CB} = 1.0\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )	Figure 1 $C_{cb}$	—	0.21	0.3	pF
<b>FUNCTIONAL TESTS</b>					
Power Gain at Minimum Noise Figure ( $V_{CE} = 1.0\text{ Vdc}$ , $I_C = 0.5\text{ mA}$ , $f = 1.0\text{ GHz}$ )	Figures 3, 5 $G_{NFmin}$	—	12.5	—	dB
Noise Figure ( $V_{CE} = 1.0\text{ Vdc}$ , $I_C = 0.5\text{ mA}$ , $f = 1.0\text{ GHz}$ )	Figures 3, 5 $NF_{min}$	—	2.5	—	dB



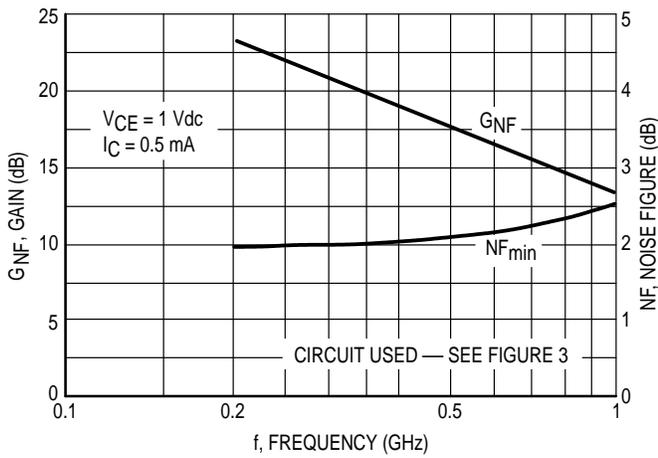
**Figure 1. Collector-Base Capacitance versus Collector-Base Voltage**



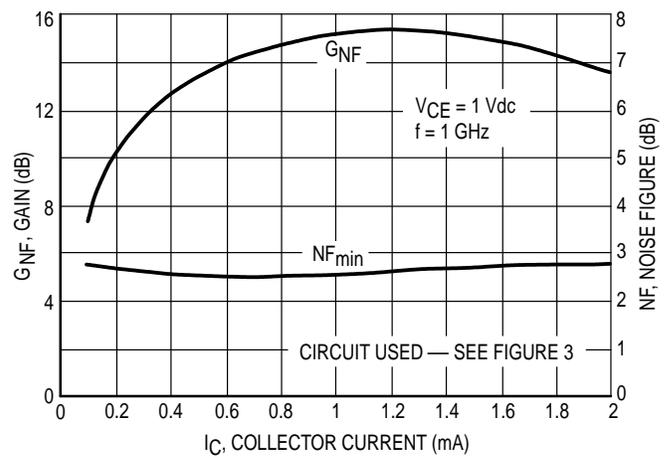
**Figure 2. Current Gain-Bandwidth Product versus Collector Current**



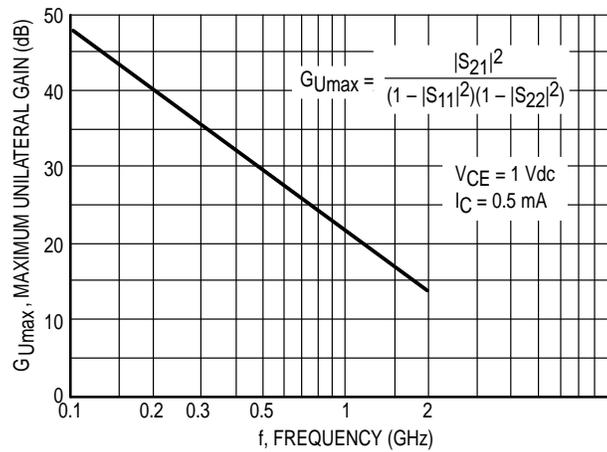
**Figure 3. Functional Circuit Schematic**



**Figure 4. Gain and Minimum Noise Figure versus Frequency**



**Figure 5. Gain and Minimum Noise Figure versus Collector Current**



**Figure 6. Maximum Unilateral Gain versus Frequency**

V <sub>CE</sub> (Vdc)	I <sub>C</sub> (mA)	f (MHz)	S <sub>11</sub>		S <sub>21</sub>		S <sub>12</sub>		S <sub>22</sub>	
			S <sub>11</sub>	∠φ	S <sub>21</sub>	∠φ	S <sub>12</sub>	∠φ	S <sub>22</sub>	∠φ
1.0	0.1	100	0.99	-1.0	0.35	174	0.01	87	0.99	-1.0
		200	0.99	-3.0	0.35	171	0.03	86	0.99	-4.0
		500	0.97	-9.0	0.34	156	0.07	81	0.99	-9.0
		1000	0.98	-19	0.38	134	0.13	72	0.99	-21
		2000	0.98	-36	0.45	103	0.22	59	0.99	-38
	0.25	100	0.99	-1.0	0.77	175	0.01	86	0.99	-1.0
		200	0.99	-4.0	0.77	173	0.03	86	0.99	-4.0
		500	0.96	-11	0.73	160	0.06	79	0.99	-11
		1000	0.96	-23	0.75	140	0.13	70	0.98	-23
		2000	0.94	-42	0.77	110	0.21	56	0.93	-42
	0.5	100	0.99	-2.0	1.43	174	0.01	86	0.99	-1.0
		200	0.99	-5.0	1.42	172	0.03	84	0.99	-5.0
		500	0.95	-13	1.33	158	0.06	77	0.99	-12
		1000	0.92	-28	1.30	137	0.13	67	0.95	-25
		2000	0.83	-51	1.20	107	0.19	54	0.91	-43

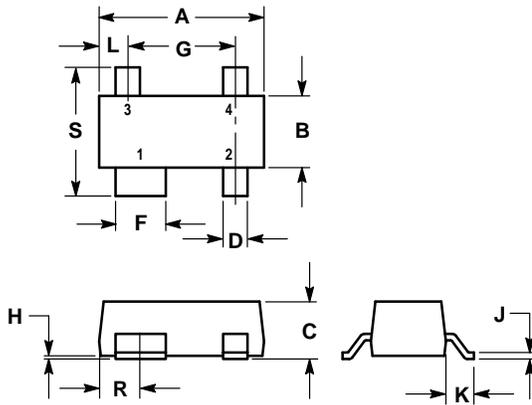
(continued)

**Table 1. Common Emitter S-Parameters**

V <sub>CE</sub> (Vdc)	I <sub>C</sub> (mA)	f (MHz)	S <sub>11</sub>		S <sub>21</sub>		S <sub>12</sub>		S <sub>22</sub>	
			S <sub>11</sub>	∠φ	S <sub>21</sub>	∠φ	S <sub>12</sub>	∠φ	S <sub>22</sub>	∠φ
1.0	1.0	100	0.97	-3.0	2.68	173	0.01	85	0.99	-2.0
		200	0.97	-8.0	2.68	169	0.03	83	0.98	-6.0
		500	0.91	-19	2.42	152	0.06	74	0.96	-15
		1000	0.82	-37	2.22	128	0.11	62	0.89	-29
		2000	0.63	-59	1.74	97	0.17	53	0.80	-46
	2.0	100	0.93	-6.0	4.55	169	0.01	84	0.99	-4.0
		200	0.92	-13	4.3	163	0.03	81	0.98	-9.0
		500	0.81	-29	3.8	142	0.06	69	0.91	-19
		1000	0.62	-52	3.1	115	0.10	59	0.81	-31
		2000	0.40	-66	2.0	85	0.14	55	0.75	-44
3.0	0.1	100	0.99	-1.0	0.34	175	0.01	88	0.99	-1.0
		200	0.99	-3.0	0.34	172	0.03	86	0.99	-3.0
		500	0.99	-8.0	0.32	157	0.06	81	0.99	-9.0
		1000	0.99	-18	0.36	137	0.11	73	0.99	-20
		2000	0.99	-34	0.43	107	0.20	61	0.99	-37
	0.25	100	0.99	-1.0	0.76	175	0.01	86	0.99	-1.0
		200	0.99	-4.0	0.76	173	0.03	86	0.99	-4.0
		500	0.98	-10	0.72	161	0.06	80	0.99	-10
		1000	0.98	-21	0.75	143	0.11	72	0.99	-22
		2000	0.97	-40	0.75	113	0.19	59	0.98	-39
	0.5	100	0.99	-2.0	1.4	175	0.01	86	0.99	-1.0
		200	0.99	-5.0	1.42	172	0.03	84	0.99	-4.0
		500	0.96	-12	1.3	159	0.06	78	0.99	-11
		1000	0.93	-25	1.3	141	0.11	68	0.96	-23
		2000	0.87	-47	1.2	111	0.18	57	0.93	-41
	1.0	100	0.97	-3.0	2.67	174	0.01	85	0.99	-2.0
		200	0.98	-7.0	2.67	170	0.02	84	0.98	-6.0
		500	0.93	-17	2.42	154	0.06	76	0.97	-14
		1000	0.84	-34	2.29	133	0.10	65	0.91	-26
		2000	0.67	-55	1.82	101	0.16	56	0.85	-43
	2.0	100	0.95	-5.0	4.64	172	0.01	85	0.99	-3.0
		200	0.94	-10	4.62	166	0.02	81	0.99	-8.0
		500	0.85	-25	4.0	147	0.05	72	0.94	-17
		1000	0.69	-44	3.4	122	0.09	63	0.84	-29
2000		0.48	-61	2.3	91	0.13	57	0.78	-42	
5.0	0.1	100	0.99	0	0.36	175	0.01	85	0.99	-1.0
		200	0.99	-3.0	0.34	172	0.02	87	0.99	-3.0
		500	0.99	-8.0	0.32	158	0.06	82	0.99	-9.0
		1000	0.99	-17	0.36	138	0.11	74	0.99	-19
		2000	0.94	-35	0.42	108	0.20	63	0.99	-36
	0.25	100	0.99	-1.0	0.76	176	0.01	86	0.99	-1.0
		200	0.99	-3.0	0.76	174	0.02	86	0.99	-4.0
		500	0.97	-9.0	0.71	161	0.06	80	0.99	-10
		1000	0.97	-20	0.74	143	0.11	73	0.99	-21
		2000	0.97	-38	0.75	115	0.18	61	0.99	-38
	0.5	100	0.99	-1.0	1.4	175	0.01	86	0.99	-1.0
		200	0.99	-5.0	1.41	173	0.02	85	0.99	-4.0
		500	0.98	-12	1.3	159	0.06	79	0.99	-11
		1000	0.93	-25	1.3	141	0.10	70	0.97	-23
		2000	0.87	-45	1.2	111	0.17	58	0.94	-40
	1.0	100	0.98	-3.0	2.7	174	0.01	86	0.99	-2.0
		200	0.98	-7.0	2.7	170	0.02	84	0.99	-5.0
		500	0.93	-17	2.42	155	0.05	76	0.97	-13
		1000	0.85	-33	2.3	134	0.09	66	0.92	-26
		2000	0.67	-55	2.0	103	0.15	57	0.85	-42
	2.0	100	0.95	-4.0	4.6	172	0.01	86	0.99	-3.0
		200	0.94	-10	4.6	166	0.02	83	0.98	-7.0
		500	0.86	-24	3.9	148	0.05	73	0.94	-16
		1000	0.70	-43	3.4	123	0.09	64	0.86	-28
2000		0.50	-60	2.3	92	0.13	59	0.80	-40	

Table 1. Common Emitter S-Parameters (continued)

## PACKAGE DIMENSIONS



- NOTES:  
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
 2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.80	3.04	0.110	0.120
B	1.20	1.39	0.047	0.055
C	0.84	1.14	0.033	0.045
D	0.39	0.50	0.015	0.020
F	0.79	0.93	0.031	0.037
G	1.78	2.03	0.070	0.080
H	0.013	0.10	0.0005	0.004
J	0.08	0.15	0.003	0.006
K	0.46	0.60	0.018	0.024
L	0.445	0.60	0.0175	0.024
R	0.72	0.83	0.028	0.033
S	2.11	2.48	0.083	0.098

- STYLE 1:  
 PIN 1. COLLECTOR  
 2. EMITTER  
 3. EMITTER  
 4. BASE

**CASE 318A-05  
 ISSUE J**

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MRF9331LT1/D

